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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/773,754	02/02/2001	Ming-Dou Ker	H000039	6902
27760	7590	06/06/2002		
INTELLECTUAL PROPERTY SOLUTIONS, P.L.L.C. 1300 PENNSYLVANIA AVENUE N.W. SUITE 700 WASHINGTON, DC 20004			EXAMINER	
			SEFER, AHMED N	
		ART UNIT	PAPER NUMBER	
		2826		

DATE MAILED: 06/06/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	Application No.	Applicant(s)
	09/773,754	KER ET AL.
Examiner	Art Unit	
A. Sefer	2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

- 1) Responsive to communication(s) filed on 12 March 2002.
- 2a) This action is FINAL.                    2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

- 4) Claim(s) 1-19 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) Claim(s) 15-18 is/are allowed.
- 6) Claim(s) 1,3,5,6,8,10,12,13 and 19 is/are rejected.
- 7) Claim(s) 2,4,7,9,11 and 14 is/are objected to.
- 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on \_\_\_\_\_ is/are: a) accepted or b) objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) The proposed drawing correction filed on \_\_\_\_\_ is: a) approved b) disapproved by the Examiner.  
If approved, corrected drawings are required in reply to this Office action.
- 12) The oath or declaration is objected to by the Examiner.

#### Priority under 35 U.S.C. §§ 119 and 120

- 13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) All b) Some \* c) None of:  
1. Certified copies of the priority documents have been received.  
2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  
\* See the attached detailed Office action for a list of the certified copies not received.
- 14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).  
a) The translation of the foreign language provisional application has been received.
- 15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

#### Attachment(s)

- |  |   |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)                  | 4) <input type="checkbox"/> Interview Summary (PTO-413) Paper No(s). _____  |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)         | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____ | 6) <input type="checkbox"/> Other: _____                                    |

**DETAILED ACTION**

***Response to Amendment***

1. The amendment filed on March 12, 2002 has been entered.

***Specification***

2. The specification is objected to as failing to provide proper antecedent basis for the claimed subject matter. See 37 CFR 1.75(d)(1) and MPEP § 608.01(o). Correction of the following is required: The "said gate" recited in claims 3 and 10, which depend on claims 1 and 8 respectively, has not been introduced.

***Claim Rejections - 35 USC § 102***

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

4. Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Ker et al. US Patent 5,637,900.

Ker et al disclose (see fig. 8) a semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising a substrate of a first conductivity type forming a base for said semiconductor structure; a first region 623 of a second conductivity type within said substrate for forming a drain of a first MOS transistor P2; a second region 620 of the second

conductivity type within said substrate for forming a source of the first MOS transistor; a third region of the second conductivity type (unnumbered) for forming a source of a second MOS transistor, wherein a fourth region (unnumbered) of first conductivity type is disposed between the second region of said first MOS transistor and the third region of the second MOS transistor for surrounding said first MOS transistor with an additional pick-up diffusion to restrain a turn-on of said first MOS transistor.

5. Claim 5 is rejected under 35 U.S.C. 102(b) as being anticipated by Ker et al. US Patent No. 5,637,900.

Ker et al disclose in fig. 8 a semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising a substrate of a first conductivity type forming a base for said semiconductor structure; a pair of first regions 620/623 of a second conductivity type within said substrate for defining a first channel region 810 of the second conductivity type for a first MOS transistor P2; and a pair of second regions 650 of a second conductivity type within said substrate for defining a second channel region 820 of the second conductivity type for a second MOS transistor P5, wherein the channel length of said first channel region is greater than the channel length of said second channel region to reduce a turn-on speed of said first MOS transistor.

6. Claim 8 is rejected under 35 U.S.C. 102(b) as being anticipated by Ker et al. US Patent No. 5,637,900.

Ker et al disclose (see fig. 8 and col. 12, lines 10-13) a semiconductor structure

for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising a p-type substrate forming a base for said semiconductor structure; a first N+ region 623 within said substrate for forming a drain of a first MOS transistor P2; a second N+ region 620 within said substrate for forming a source of the first MOS transistor; a third N+ region (unnumbered) within said substrate for forming a source of a second MOS transistor, wherein a P+ region (unnumbered) is disposed between the second region of said first MOS transistor and the third region of the second MOS transistor for surrounding said first MOS transistor with an additional pick-up diffusion to restrain a turn-on of said first MOS transistor.

7. Claim 12 is rejected under 35 U.S.C. 102(b) as being anticipated by Ker et al. US Patent No. 5,637,900.

Ker et al disclose (see fig. 8 and col. 12, lines 10-13 a semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising a p-type substrate forming a base for said semiconductor structure; a pair of first N+ regions 620/623 within said substrate for defining a first n-channel region 810 for a first MOS transistor P2; and a pair of second N+ regions 650 within said substrate for defining a second n-channel region 820 for a second MOS transistor P5, wherein the channel length of said first channel region is greater than the channel length of said second channel region to reduce a turn-on speed of said first MOS transistor.

8. Claim 19 is rejected under 35 U.S.C. 102(b) as being anticipated by Ker et al. US Patent No. 5,637,900.

Ker et al disclose (see fig. 6) a semiconductor structure for electrostatic discharge (ESD) protection, comprising at least one ESD protection device P3; and at least one guarded device P1 which is turned-on by a turn-on restrain means, wherein the ESD protection device can be turned-on before the guarded device is turned on.

***Claim Rejections - 35 USC § 103***

9. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

10. Claims 3, 6, 10 and 13, as understood, are rejected under 35 U.S.C. 103(a) as being unpatentable over Ker et al. US Patent No. 5,637,900 in view of admitted prior art (APA).

Ker et al disclose all the claimed subject matter but fail to teach a pre-puffer circuit coupled to a gate of MOS transistor or a channel and an output pad coupled to a first region or regions of a MOS transistor.

The APA disclose in fig. 5 a pre-puffer coupled to a gate of a MOS transistor or indirectly to a channel; and an output pad coupled to a region or regions of a MOS transistor.

Therefore, it would have been obvious to one skilled in the art at the time the invention was made to incorporate the teachings of the APA with Ker et al, since that would reduce transient contributions to a response.

***Allowable Subject Matter***

11. Claims 15-18 are allowed.
12. Claims 2, 4, 7, 9, 11 and 14 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

***Conclusion***

13. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to A. Sefer whose telephone number is (703) 605-1227.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on (703) 308-6601.

ANS

June 3, 2002

~~NATHAN J. FLYNN  
SUPERVISORY PATENT EXAMINER  
TECHNOLOGY CENTER 2800~~